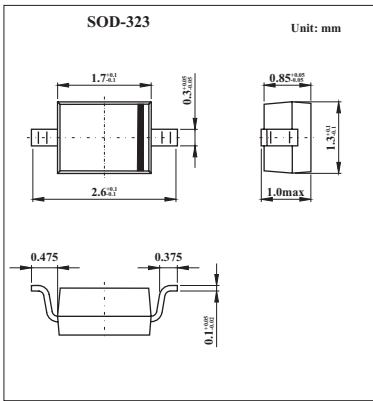


Silicon Epitaxial Planar Pin Diode

HVU133

■ Features

- Low capacitance.(C=1.0pF max)
- Low forward resistance. (rf=0.7 Ω max)



■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Value	Unit
Reverse voltage	V_R	30	V
Power dissipation	P_d	150	mW
Junction temperature	T_j	125	℃
Storage temperature	T_{stg}	-55 to +125	℃

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse voltage	V_R	$I_R = 1 \mu A$	30			V
Reverse current	I_R	$V_R = 25 V$			100	nA
Forward voltage	V_F	$I_F = 2 mA$			0.85	V
Capacitance	C1	$V_R = 1 V, f = 1 MHz$			1.0	pF
	C6	$V_R = 6 V, f = 1 MHz$			0.9	
Forward resistance	r_f	$I_F = 2 mA, f = 100 MHz$		0.55	0.7	Ω

■ Marking

Marking	P3
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